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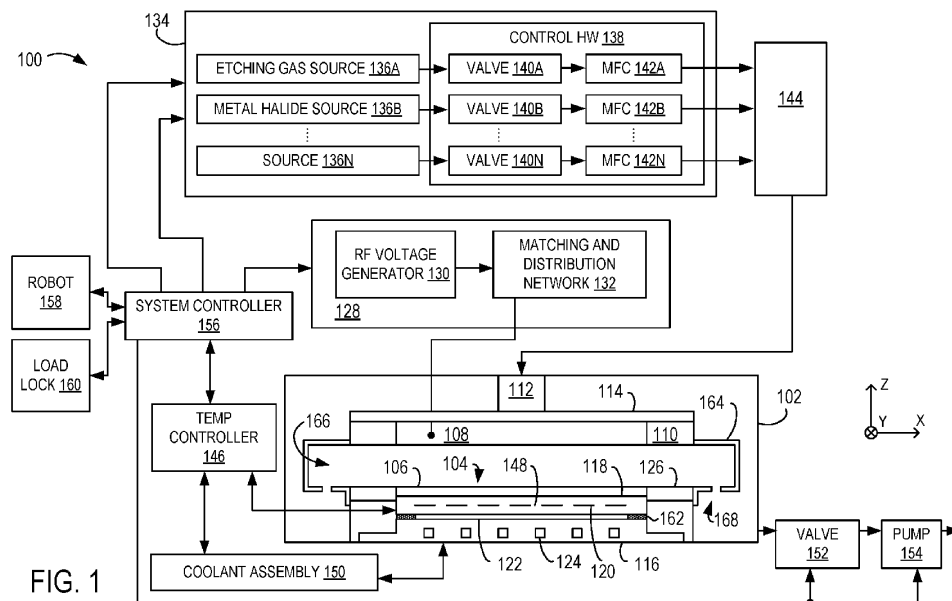
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(54) Title: CONTEMPORANEOUS ETCHING OF OXIDE AND DEPOSITION OF METAL-CONTAINING SUBSTANCE ON PATTERNING MASK



(57) Abstract: A method of etching a feature in an oxide layer formed on a substrate comprises introducing a gas mixture comprising an etching agent and a metal halide into a plasma formed in a processing chamber in which a substrate is located. The substrate comprises an oxide layer partially covered with a patterning mask. The method further comprises contemporaneously etching the feature in an unmasked portion of the oxide layer and depositing a substance containing a metal from the metal halide on the patterning mask.

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